

[FABRICATION METHOD FOR SEMICONDUCTOR HOLE]

Abstract of Disclosure

A fabrication method for a semiconductor hole is described. The method provides a circular or a elliptical hole pattern. A first exposure is performed with a first photomask that comprises a plurality of diagonally allocated square patterns wherein the square patterns on the first photomask are tilted at an angle of 45 degrees. Thereafter, a second exposure is performed using a second photomask, wherein patterns on the second photomask are mirror images to those on the second photomask to prevent the peeling of the photoresist at between the diagonally allocated hole patterns.

Figures